

# Akihiko Ohi

## List of Publications by Year in descending order

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23  
papers

440  
citations

932766

10  
h-index

713013

21  
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23  
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23  
docs citations

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times ranked

668  
citing authors

#	ARTICLE	IF	CITATIONS
1	Infrared Perfect Absorbers Fabricated by Colloidal Mask Etching of Al <sub>2</sub> O <sub>3</sub> Al Trilayers. ACS Photonics, 2015, 2, 964-970.	3.2	172
2	An On-Chip Quad-Wavelength Pyroelectric Sensor for Spectroscopic Infrared Sensing. Advanced Science, 2019, 6, 1900579.	5.6	31
3	Hafnium silicate gate dielectrics in GaN metal oxide semiconductor capacitors. Applied Physics Express, 2019, 12, 011009.	1.1	28
4	Organic $\bar{n}$ -type thermoelectric module supported by photolithographic mold: a working hypothesis of sticky thermoelectric materials. Science and Technology of Advanced Materials, 2018, 19, 517-525.	2.8	27
5	MEMS-Based Wavelength-Selective Bolometers. Micromachines, 2019, 10, 416.	1.4	19
6	Electrical properties of anatase TiO <sub>2</sub> films by atomic layer deposition and low annealing temperature. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2014, 32, .	0.6	18
7	Investigation of Al <sub>2</sub> O <sub>3</sub> /GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. AIP Advances, 2019, 9, .	0.6	17
8	Low-energy ion scattering spectroscopy and reflection high-energy electron diffraction of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2017, 56, 128004.	0.8	16
9	Improved leakage current properties of ZrO <sub>2</sub> /(Ta/Nb) <sub>x</sub> -Al <sub>2</sub> O <sub>3</sub> /ZrO <sub>2</sub> nanolaminate insulating stacks for dynamic random access memory capacitors. Thin Solid Films, 2018, 655, 48-53.	0.8	16
10	A MEMS-Based Quad-Wavelength Hybrid Plasmonic Pyroelectric Infrared Detector. Micromachines, 2019, 10, 413.	1.4	16
11	Role of the (Ta/Nb) <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> interface on the flatband voltage shift for Al <sub>2</sub> O <sub>3</sub> /(Ta/Nb) <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> multilayer charge trap capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2015, 33, .	0.9	10
12	Change of characteristics of n-GaN MOS capacitors with Hf-rich HfSiO <sub>x</sub> gate dielectrics by post-deposition annealing. Microelectronic Engineering, 2019, 216, 111036.	1.1	9
13	Improvement of smooth surface of RuO <sub>2</sub> bottom electrode on Al <sub>2</sub> O <sub>3</sub> buffer layer and characteristics of RuO <sub>2</sub> /TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> /RuO <sub>2</sub> capacitors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	8
14	Electron microscopy and ultraviolet photoemission spectroscopy studies of native oxides on GaN(0001). Japanese Journal of Applied Physics, 2018, 57, 098003.	0.8	8
15	The Effect of Physical and Chemical Cues on Hepatocellular Function and Morphology. International Journal of Molecular Sciences, 2014, 15, 4299-4317.	1.8	7
16	Nanostructures Control the Hepatocellular Responses to a Cytotoxic Agent $\epsilon$ -Cisplatin. BioMed Research International, 2015, 2015, 1-10.	0.9	7
17	Interface characteristics of $\bar{I}^2$ -Ga <sub>2</sub> O <sub>3</sub> /Al <sub>2</sub> O <sub>3</sub> /Pt capacitors after postmetallization annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	7
18	Correlation between SiO <sub>2</sub> growth rate and difference in electronegativity of metal oxide underlayers for plasma enhanced atomic layer deposition using tris(dimethylamino)silane precursor. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	6

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19	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2018, 36, 061206.	0.6	5
20	Nanoantenna Structure with Mid-Infrared Plasmonic Niobium-Doped Titanium Oxide. Micromachines, 2020, 11, 23.	1.4	5
21	Influence of Oxidant Gas of Atomic Layer Deposition on Electrical Characteristics of Al <sub>2</sub> O <sub>3</sub> films. Vacuum and Surface Science, 2018, 61, 280-285.	0.0	5
22	Influence of HfO <sub>2</sub> and SiO <sub>2</sub> interfacial layers on the characteristics of n-GaN/HfSiO <sub>x</sub> capacitors using plasma-enhanced atomic layer deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	2
23	Aluminum infrared plasmonic perfect absorbers fabricated by colloidal lithography. , 2015, , .		1